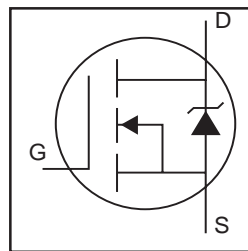


HEXFET® Power MOSFET Die in Wafer Form



60 V
 Size 4.0
 $R_{ds(on)}=0.034\Omega$
 5" Wafer

Electrical Characteristics (Wafer Form)

| Parameter | Description | Guaranteed (Min/Max) | Test Conditions |
|---------------|--------------------------------------|----------------------|---|
| $V_{(BR)DSS}$ | Drain-to-Source Breakdown Voltage | 60V Min. | $V_{GS} = 0V, I_D = 100\mu A$ |
| $R_{DS(on)}$ | Static Drain-to-Source On-Resistance | 0.034 Ω Max. | $V_{GS} = 10V, I_D = 5.0A$ |
| $V_{GS(th)}$ | Gate Threshold Voltage | 2.1V Min. | $V_{DS} = 5.0V, I_D = 250\mu A$ |
| I_{DSS} | Drain-to-Source Leakage Current | 100 μA Max. | $V_{DS} = 60V, V_{GS} = 0V, T_J = 25^\circ C$ |
| I_{GSS} | Gate-to-Source Leakage | $\pm 10\mu A$ Max. | $V_{GS} = \pm 20V$ |
| T_J | Operating Junction and | 125 $^\circ C$ Max. | |
| T_{STG} | Storage Temperature Range | | |

Mechanical Data

| | |
|---|---|
| Nominal Backmetal Composition, Thickness: | Cr-NiV-Ag (1kA°-2kA°-2.5kA°) |
| Nominal Front Metal Composition, Thickness: | 99% Al, 1% Si (0.004mm) |
| Dimensions: | 0.170" x 0.180" (4.32mm x 4.57 mm) |
| Wafer Diameter: | 125mm with 100 flat |
| Wafer thickness: | 0.375mm + / -0.020mm |
| Relevant Die Mechanical Dwg. Number | 01-5018 |
| Minimum Street Width | 0.084 mm |
| Reject Ink Dot Size | 0.51mm Diameter Minimum |
| Recommended Storage Environment: | Store in original container, in dessicated nitrogen, with no contamination |
| Recommended Die Attach Conditions | For optimum electrical results, die attach temperature should not exceed 300C |

Reference Standard IR packaged part (for design) : IRFZ44

Die Outline

